

Product Features

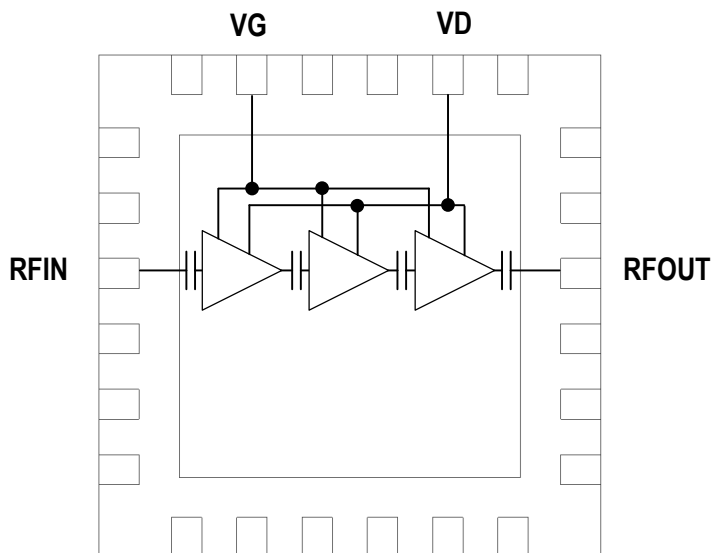
- Frequency Range: 8.0-11 GHz
- Output Power ($P_{IN} = 18$ dBm): 42 dBm
- PAE ($P_{IN} = 18$ dBm): 44%
- Small Signal Gain: 34.5 dB
- Input Return Loss: > 10 dB
- Output Return Loss: > 9.5 dB
- Recommended Bias: $V_D = 24$ V, $I_{DQ} = 210$ mA
- Package Dimensions: 5×5×1.0 mm

Performance is typical at room temperature. Please reference electrical specification table and data plots for more details.



5 mm × 5 mm QFN package

Functional Block Diagram



Description

The HR150XQ3 is a fully integrated 3-stage power amplifier MMIC designed for radar applications, covering frequency range from 8.0 GHz to 11.0 GHz. The device delivers saturated output power of 15 W and has more than 44.0% drain efficiency with operating drain voltage of 24 V.

Applications

- Satcom
- Commercial and Military Radar
- Communications

DC Characteristics

PARAMETER	SYMBOL	VALUE	UNIT
Drain Voltage	V_D	24	V
Drain Quiescent Current	I_{DQ}	210	mA
Gate Voltage Range	V_G	-2.0 to -1.85	V
Operating Temperature Range		-40 to 85	°C

1. Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.
2. Gate voltage shown are typical, can be adjusted to set required drain current.
3. Control Voltages can use down to -10 V.

Absolute Maximum Ratings

PARAMETER	SYMBOL	MIN VALUE	MAX VALUE	UNIT
Drain Voltage	V_D	-	29.5	V
Drain Current	I_{DIDQ}	-	2000	mA
Gate Voltage Range	V_G	-5	0	V
Gate Current	I_G	-	10	mA
TX Input Power(@ 85°C, Pulse, 50 Ohm)		-	21	dBm
Mounting Temperature		-55	150	°C

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied. Extended application of Absolute Maximum Rating conditions may reduce device reliability.

Electrical Specifications

Test conditions unless otherwise noted: $V_D = 24$ V, $I_{DQ} = 210$ mA

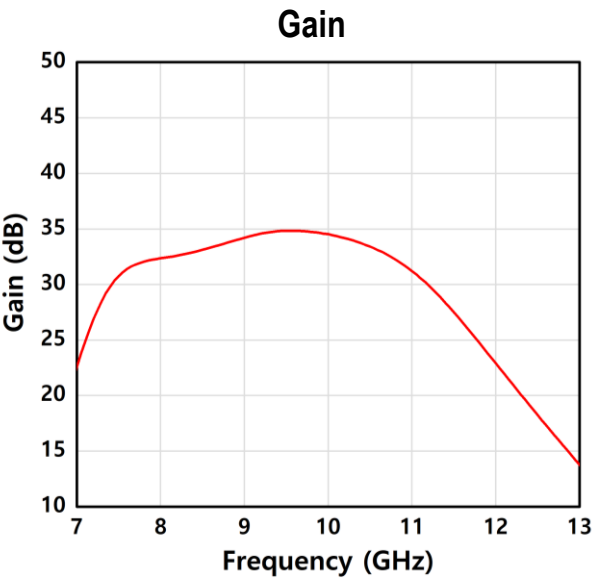
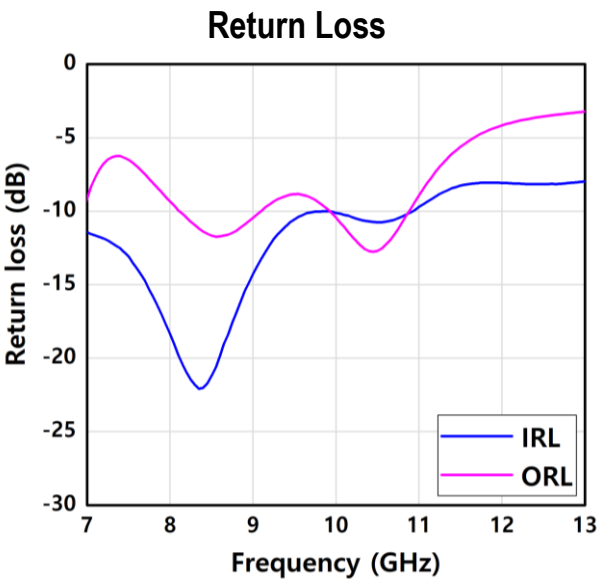
Data de-embedded to device reference plane, 25 °C.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Frequency	f	8.0		11	GHz
Small signal gain	G		34.5		dB
Input Return Loss	IRL		10		dB
Output return loss	ORL		9.5		dB
Output Power*	P_{sat}		42.0		dBm
PAE*	PAE		44.0		%

* $P_{in} = 18$ dBm, PW 100 μ s / DC 10% pulsed CW signal

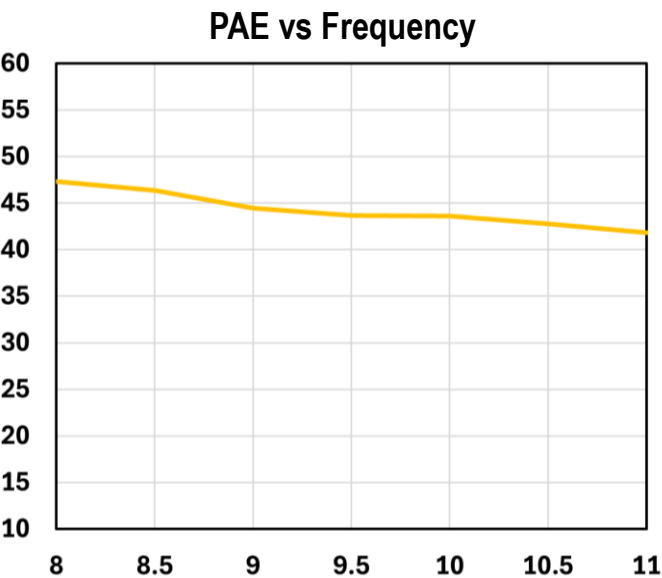
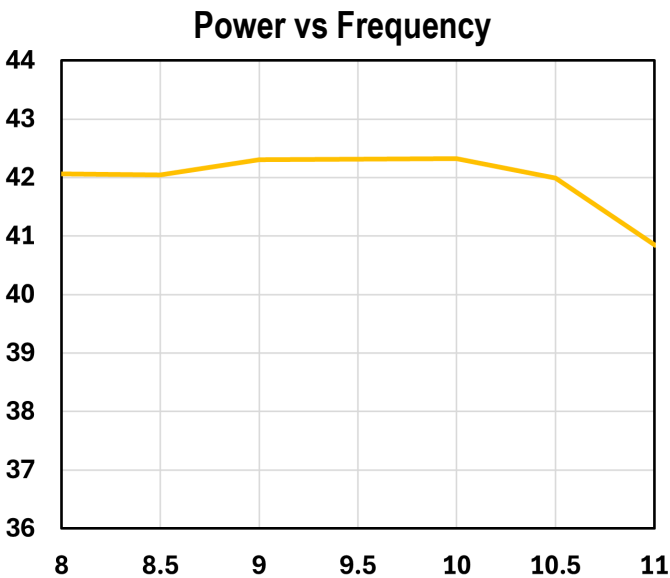
Small Signal Performance

Test Conditions unless otherwise stated: $V_D = 24\text{ V}$, $I_{DQ} = 210\text{ mA}$, $25\text{ }^{\circ}\text{C}$



Large Signal Performance, Transmit

Test Conditions unless otherwise stated: $V_D = 24\text{ V}$, $I_{DQ} = 210\text{ mA}$
Pulse Mode, $P_{in} = 18\text{ dBm}$, $PW = 100\text{ }\mu\text{s}$, $DC = 10\%$, $25\text{ }^\circ\text{C}$

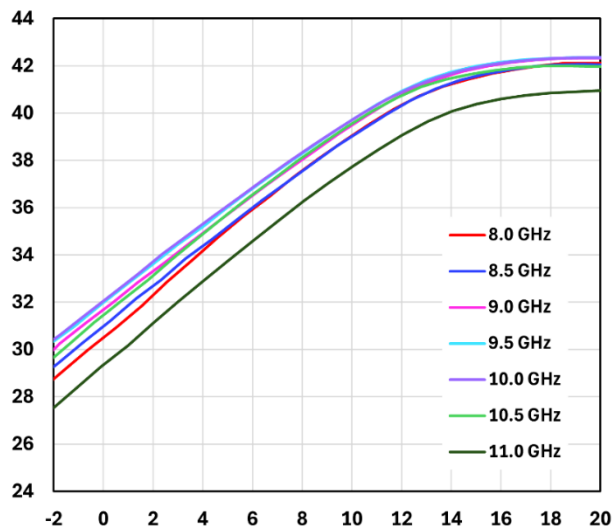


Power Sweep, Transmit

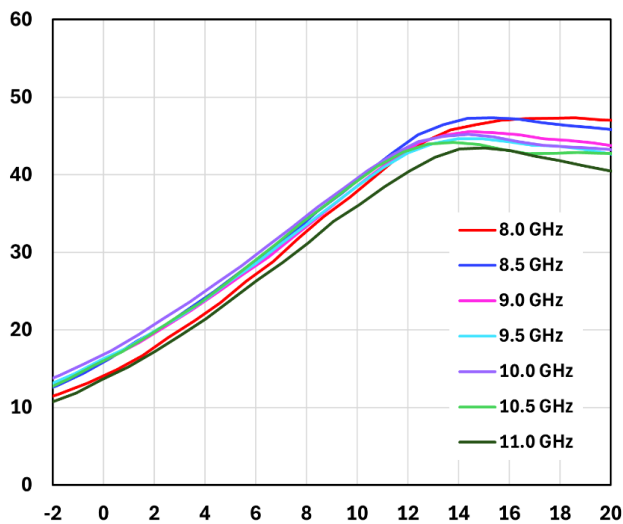
Test Conditions unless otherwise stated: $V_D = 24$ V, $I_{DQ} = 210$ mA

Pulse Mode, $PW = 100$ μ S, $DC = 10\%$, 25 $^{\circ}$ C

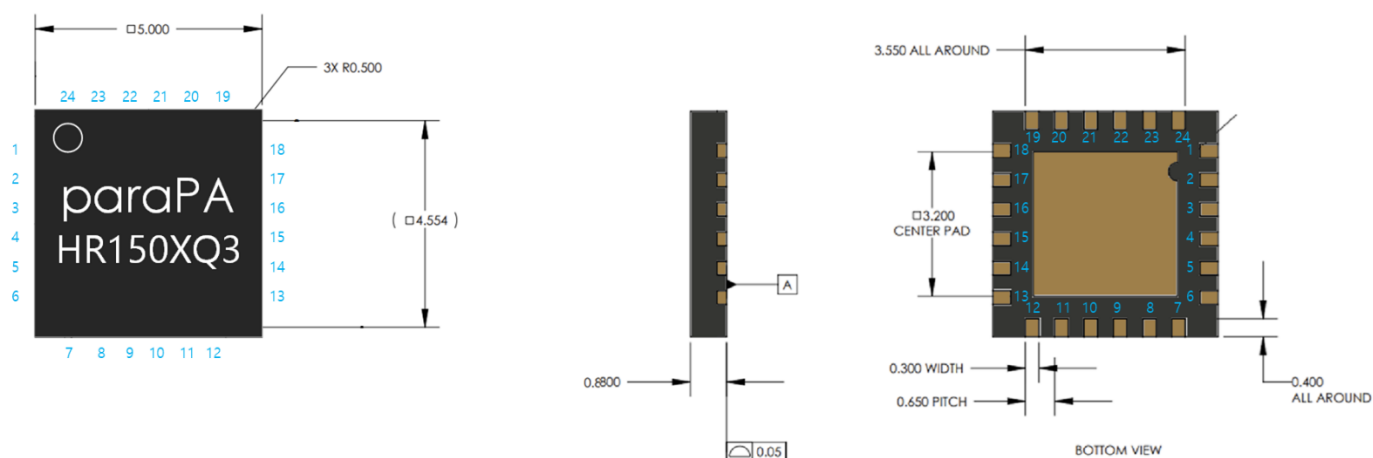
Power vs Pin



PAE vs Pin



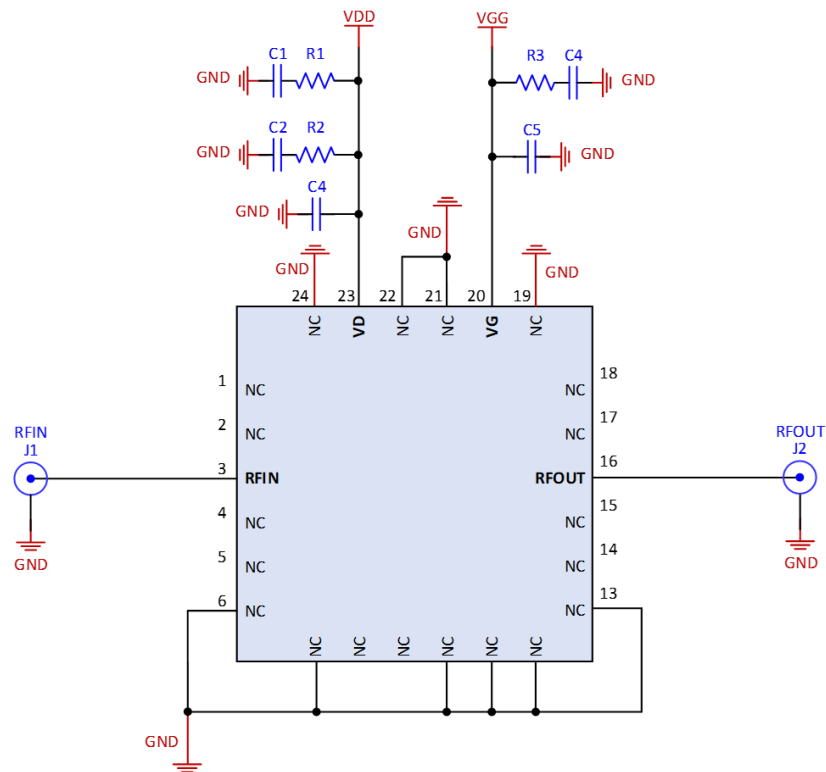
Mechanical Drawing & Pad Description



Dimensions in mm

Pin Number	Label	Description
Bottom Pad	GND	GROUND
3	RFIN	RF input. 50 Ω , DC blocked, pad connected to ground
16	RFOUT	RF output. 50 Ω , DC blocked, pad connected to ground
20	VD	Drain voltage. Bypass network required
23	VG	Gate voltage. Bypass network required
1, 2, 4-15, 17-19, 21, 22, 24	N/C	No Internal Connections. Connection to PCB ground recommended

Application Circuit



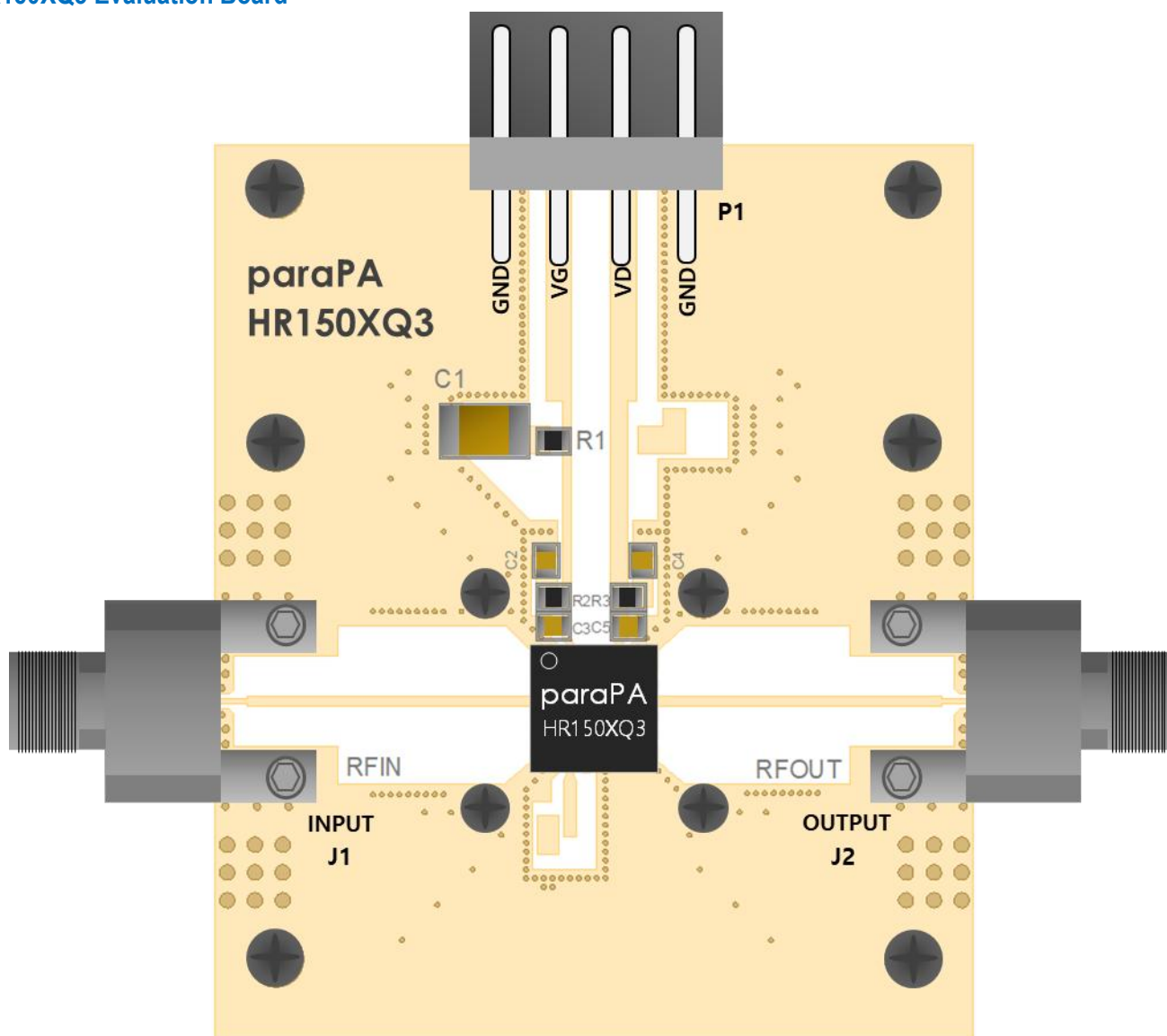
Bias-up Procedure

1. Set I_D limit to 1800 mA, I_G limit to 10 mA
2. Apply -4 V to V_G
3. Apply +24 V to V_D ; ensure I_{DQ} is approx. 0mA
4. Adjust V_G until $I_{DQ} = 250$ mA
5. Turn on RF supply

Bias-down Procedure

1. Turn off RF signal
2. Reduce V_G to -4 V; ensure I_{DQ} is approx. 0 mA
3. Set V_D to 0 V
4. Turn off V_D supply
- 5 Turn off V_G supply

HR150XQ3 Evaluation Board



RF Layer is 0.008" thick Rogers Corp. RO4003C ($\epsilon_r = 3.35$). Metal layers are 0.5 oz. copper. The microstrip line at the connector interface is optimized for the With-wave end launch connector NE02FS001.

Ref. Des.	Component	Value	Manuf.	Part Number
C1	SMT Cap.	10 uF, 1206 size, 10%, X5R, 50 V	Various	
C2, C4	SMT Cap.	0.1 uF, 0402 size, 10%, X7R, 50 V	Various	
C3, C5	SMT Cap.	1 nF, 0402 size, 10%, X7R, 50 V	Various	
R1	SMT Res.	0 Ohm, 0402 size, 0.1 W, 50 V	Various	
R2, R3	SMT Res.	10 Ohm, 0402 size, 1%, 0.625 W, 50 V	Various	
J1, J2	RF Connectors		With-wave	NE02FS001

Electrostatic Discharge (ESD) Classifications

PARAMETER	SYMBOL	CLASS	TEST METHODOLOGY
Human body model	HBM	TBD	TBD
Charge device model	CDM	TBD	TBD

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